Prof. Wu Lu
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Journal Publications: >150
Total number of citation: >1000
H-index: 18

Wu Lu (SM'01) received the Ph.D. degree in physical electronics and optoelectronics from Southeast University, Nanjing, China, in 1994. He has been a Faculty Member with the Department of Electrical and Computer Engineering, The Ohio State University, Columbus, OH, USA, since 2002. His current research interests include nanofabrication and nano-electronics, semiconductor physics and devices, solid state chemical/biological sensors, energy storage devices, and bionanotechnology.

Selected publications:

1. AlGaN/GaN HEMTs on SiC with over 100 GHz f(T) and low microwave noise
By: Lu, W; Yang, JW; Khan, MA; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 48 Issue: 3 Pages: 581-585 Published: MAR 2001
Citation number: 164

2. AlGaN/GaN HEMTs on SiC with f(T) of over 120-GHz
By: Kumar, V; Lu, W; Schwindt, R; et al., IEEE ELECTRON DEVICE LETTERS Volume: 23 Issue: 8 Pages: 455-457 Published: AUG 2002
Citation number: 123

3. Barrier heights of Schottky contacts on strained AlGaN/GaN heterostructures: Determination and effect of metal work functions
By: Lin, ZJ; Lu, W; Lee, J; et al. APPLIED PHYSICS LETTERS Volume: 82 Issue: 24 Pages: 4364-4366 Published: JUN 16 2003
Citation number: 45

4. Nanochannel electroporation delivers precise amounts of biomolecules into living cells
By: Boukany, Pouyan E.; Morss, Andrew; Liao, Wei-ching; et al. NATURE NANOTECHNOLOGY Volume: 6 Issue: 11 Pages: 747-754 Published: NOV 2011
Citation number: 41

5. DC, RF, and, microwave noise performance of AlGaN-GaN field effect transistors dependence of aluminum concentration
By: Lu, W; Kumar, V; Piner, EL; et al. IEEE TRANSACTIONS ON ELECTRON DEVICES Volume: 50 Issue: 4 Pages: 1069-1074 Published: APR 2003
Citation number: 41

6. AlGaN/GaN Schottky diode hydrogen sensor performance at high temperatures with different catalytic metals
By: Song, JH; Lu, W; Flynn, JS; et al. SOLID-STATE ELECTRONICS Volume: 49 Issue: 8 Pages: 1330-1334 Published: AUG 2005
Citation number: 39

7. Thermal stability of Schottky contacts on strained AlGaN/GaN heterostructures
By: Lin, ZJ; Kim, H; Lee, J; et al. APPLIED PHYSICS LETTERS Volume: 84 Issue: 9 Pages: 1585-1587 Published: MAR 1 2004
Citation number: 35

8. Effect of H-2 on the etch profile of InP/InGaAsP alloys in Cl-2/Ar/H-2 inductively coupled plasma reactive ion etching chemistries for photonic device fabrication
By: Rommel, SL; Jang, JH; Lu, W; et al. JOURNAL OF VACUUM SCIENCE & TECHNOLOGY B Volume: 20 Issue: 4 Pages: 1327-1330 Published: JUL-AUG 2002
Citation number: 35

9. Passivation effects in Ni/AlGaN/GaN Schottky diodes by annealing
By: Kim, Hyeongnam; Schuette, Michael; Jung, Hyunchul; et al. APPLIED PHYSICS LETTERS Volume: 89 Issue: 5 Article Number: 053516 Published: JUL 31 2006
Citation number: 32

10. Pt-AlGaN/GaN Schottky diodes operated at 800 degrees C for hydrogen sensing
By: Song, JH; Lu, W; Flynn, JS; et al. APPLIED PHYSICS LETTERS Volume: 87 Issue: 13 Article Number: 133501 Published: SEP 26 2005
Citation number: 32